



# BUK7E13-60E

N-channel TrenchMOS standard level FET

11 September 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

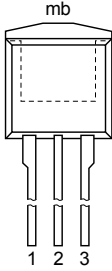
### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions                                                                                                               | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| V <sub>DS</sub>                | drain-source voltage             | T <sub>J</sub> ≥ 25 °C; T <sub>J</sub> ≤ 175 °C                                                                          | -   | -   | 60  | V    |
| I <sub>D</sub>                 | drain current                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>                                                  | -   | -   | 58  | A    |
| P <sub>tot</sub>               | total power dissipation          | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                                          | -   | -   | 96  | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                          |     |     |     |      |
| R <sub>DSon</sub>              | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>                           | -   | 9.6 | 13  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                          |     |     |     |      |
| Q <sub>GD</sub>                | gate-drain charge                | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 6.9 | -   | nC   |

## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                             | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|----------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | G      | gate                              |  <p><b>I2PAK (SOT226)</b></p> |  |
| 2   | D      | drain                             |                                                                                                                |                                                                                     |
| 3   | S      | source                            |                                                                                                                |                                                                                     |
| mb  | D      | mounting base; connected to drain |                                                                                                                |                                                                                     |

## 3. Ordering information

Table 3. Ordering information

| Type number | Package |                                              |         |
|-------------|---------|----------------------------------------------|---------|
|             | Name    | Description                                  | Version |
| BUK7E13-60E | I2PAK   | plastic single-ended package (I2PAK); TO-262 | SOT226  |

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter               | Conditions                                                                                  |                     | Min | Max | Unit |
|---------------------------|-------------------------|---------------------------------------------------------------------------------------------|---------------------|-----|-----|------|
| $V_{DS}$                  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                          |                     | -   | 60  | V    |
| $V_{DGR}$                 | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                                |                     | -   | 60  | V    |
| $V_{GS}$                  | gate-source voltage     | $T_j \leq 175\text{ °C}$ ; DC                                                               |                     | -20 | 20  | V    |
| $I_D$                     | drain current           | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>                   |                     | -   | 58  | A    |
|                           |                         | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>                  |                     | -   | 41  | A    |
| $I_{DM}$                  | peak drain current      | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a> |                     | -   | 234 | A    |
| $P_{tot}$                 | total power dissipation | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                            |                     | -   | 96  | W    |
| $T_{stg}$                 | storage temperature     |                                                                                             |                     | -55 | 175 | °C   |
| $T_j$                     | junction temperature    |                                                                                             |                     | -55 | 175 | °C   |
| <b>Source-drain diode</b> |                         |                                                                                             |                     |     |     |      |
| $I_S$                     | source current          | $T_{mb} = 25\text{ °C}$                                                                     | <a href="#">[1]</a> | -   | 58  | A    |
| $I_{SM}$                  | peak source current     | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                          |                     | -   | 234 | A    |

| Symbol               | Parameter                                    | Conditions                                                                                                                                                                                   |                        | Min | Max | Unit |
|----------------------|----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------|-----|-----|------|
| Avalanche ruggedness |                                              |                                                                                                                                                                                              |                        |     |     |      |
| $E_{DS(AL)S}$        | non-repetitive drain-source avalanche energy | $I_D = 58\text{ A}$ ; $V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ;<br>$V_{GS} = 60\text{ V}$ ; $T_{j(init)} = 25\text{ }^\circ\text{C}$ ; unclamped;<br><a href="#">Fig. 3</a> | <a href="#">[2][3]</a> | -   | 37  | mJ   |

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

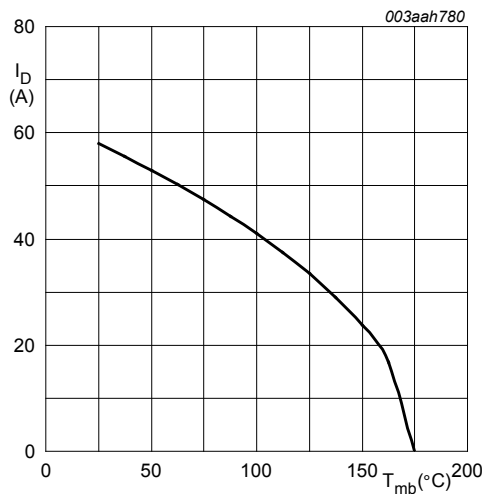


Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \geq 10\text{ V}$

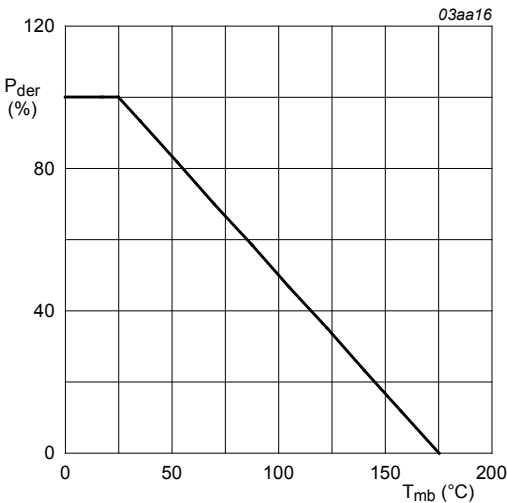


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

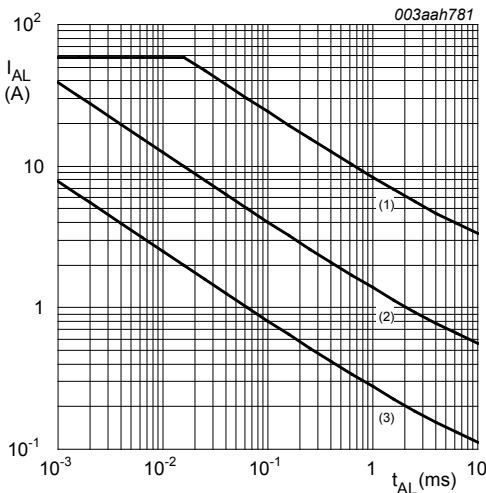


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

- (1)  $T_{j\text{ (init)}} = 25^\circ\text{C}$ ; (2)  $T_{j\text{ (init)}} = 150^\circ\text{C}$ ; (3) Repetitive Avalanche

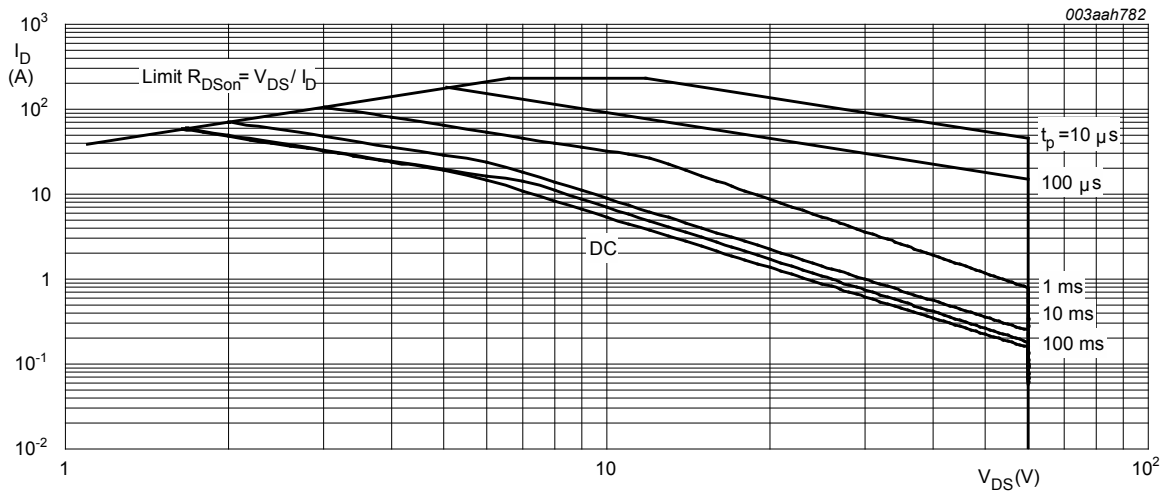


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions            | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|-----------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5                | -   | -   | 1.56 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | vertical in still air | -   | 65  | -    | K/W  |

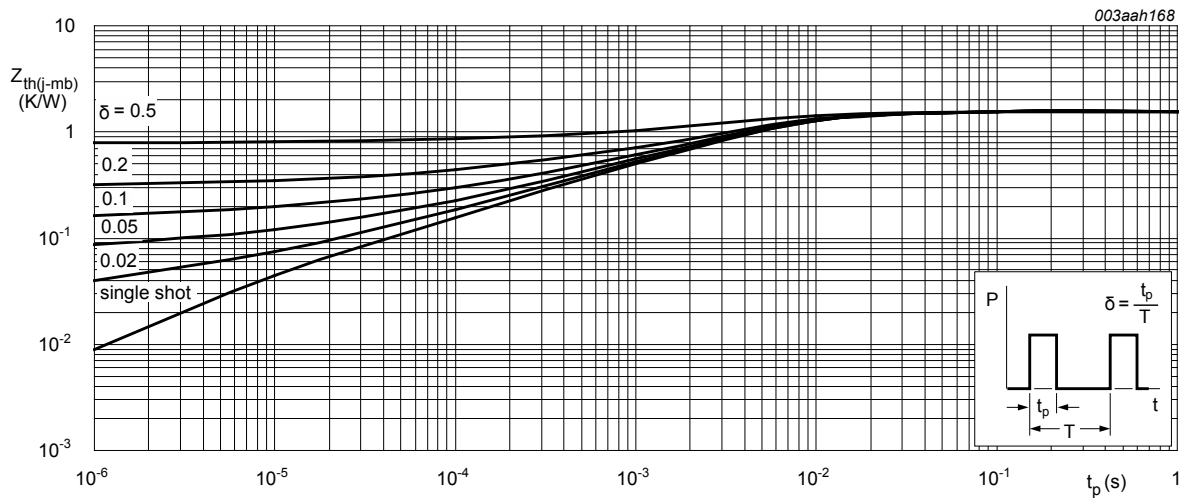


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                          |  | Min | Typ   | Max  | Unit |
|-------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------|--|-----|-------|------|------|
| Static characteristics  |                                  |                                                                                                                                     |  |     |       |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                              |  | 60  | -     | -    | V    |
|                         |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                             |  | 54  | -     | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a> |  | 2.4 | 3     | 4    | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <a href="#">Fig. 9</a>                          |  | 1   | -     | -    | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 9</a>                          |  | -   | -     | 4.5  | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                               |  | -   | 0.025 | 1    | μA   |
|                         |                                  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                                              |  | -   | -     | 500  | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                               |  | -   | 2     | 100  | nA   |
|                         |                                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                              |  | -   | 2     | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>                                      |  | -   | 9.6   | 13   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>           |  | -   | -     | 28.2 | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                     |  |     |       |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>            |  | -   | 22.9  | -    | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                                     |  | -   | 5     | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                                     |  | -   | 6.9   | -    | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                           |  | -   | 1298  | 1730 | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                                     |  | -   | 197   | 237  | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                                     |  | -   | 122   | 162  | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 45 V; R <sub>L</sub> = 3 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω                                     |  | -   | 10.8  | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                                     |  | -   | 9.2   | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                                     |  | -   | 21.9  | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                                     |  | -   | 9.8   | -    | ns   |
| L <sub>D</sub>          | internal drain inductance        | from upper edge of mounting base to centre of die ; T <sub>j</sub> = 25 °C                                                          |  | -   | 2.5   | -    | nH   |
|                         |                                  | T <sub>j</sub> = 25 °C; from drain lead 6mm from package to centre of die                                                           |  | -   | 4.5   | -    | nH   |
| L <sub>S</sub>          | internal source inductance       | measured from source lead to source bond pad ; T <sub>j</sub> = 25 °C                                                               |  | -   | 7.5   | -    | nH   |

| Symbol             | Parameter             | Conditions                                                                            | Min | Typ  | Max | Unit |
|--------------------|-----------------------|---------------------------------------------------------------------------------------|-----|------|-----|------|
| Source-drain diode |                       |                                                                                       |     |      |     |      |
| $V_{SD}$           | source-drain voltage  | $I_S = 20\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; Fig. 16          | -   | 0.84 | 1.2 | V    |
| $t_{rr}$           | reverse recovery time | $I_S = 15\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; | -   | 21.3 | -   | ns   |
| $Q_r$              | recovered charge      | $V_{DS} = 25\text{ V}$                                                                | -   | 18.1 | -   | nC   |

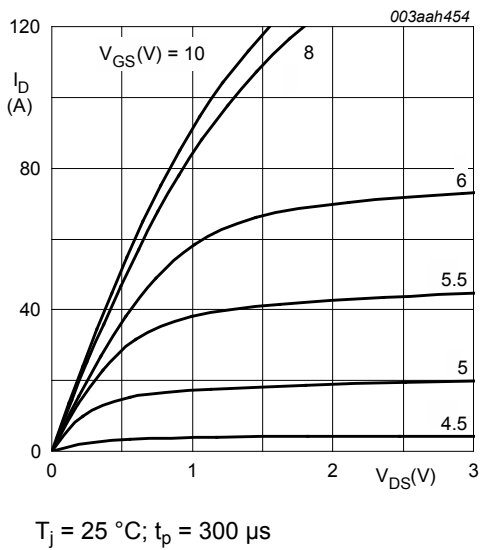


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

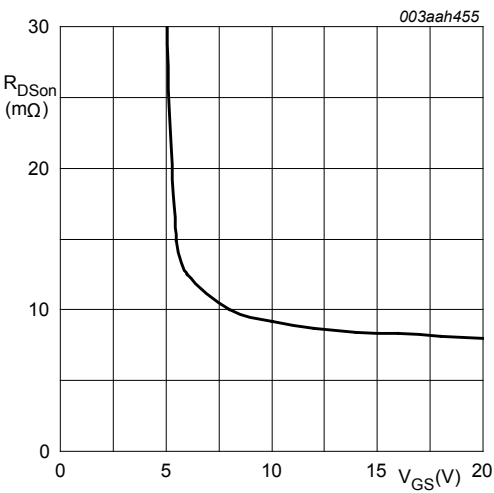


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

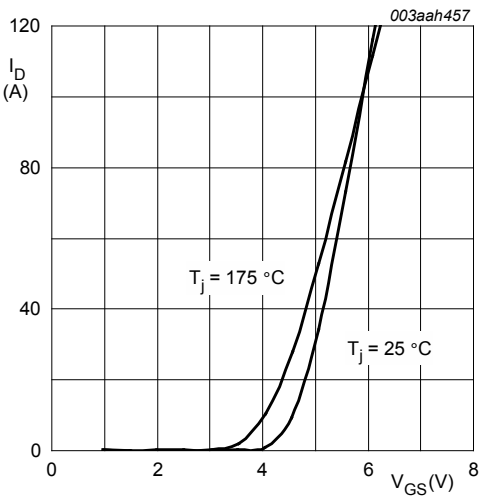


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

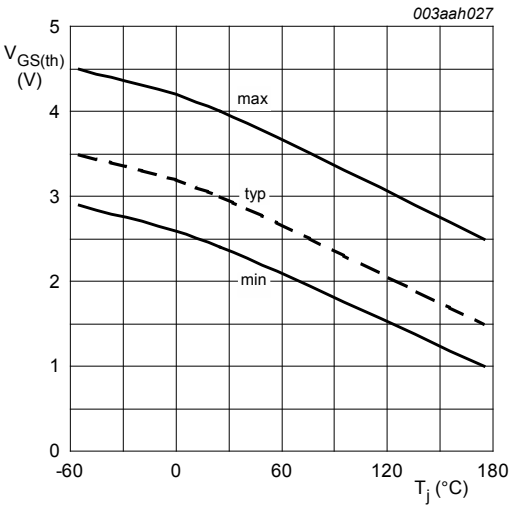


Fig. 9. Gate-source threshold voltage as a function of junction temperature

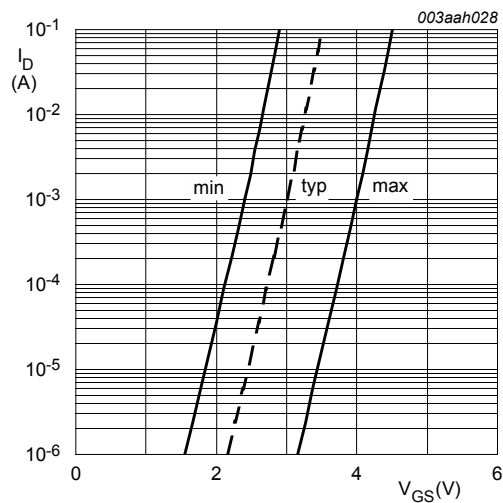


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^{\circ}\text{C}; V_{DS} = 5\text{V}$

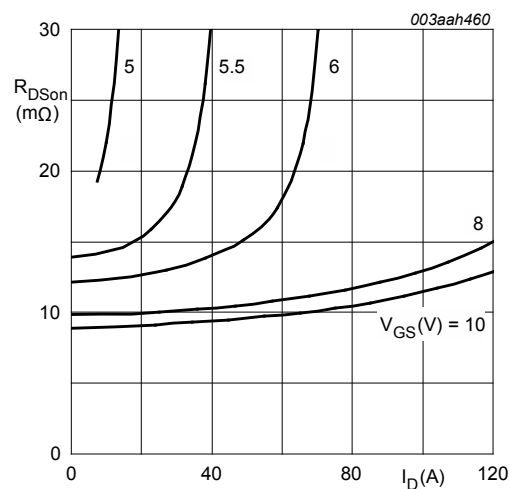


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

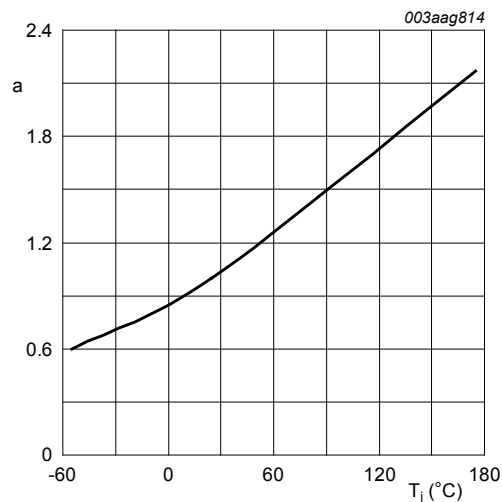


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

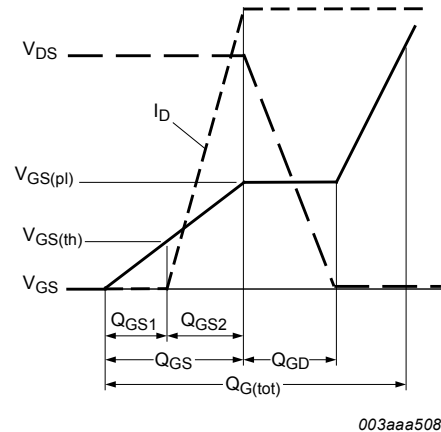


Fig. 13. Gate charge waveform definitions

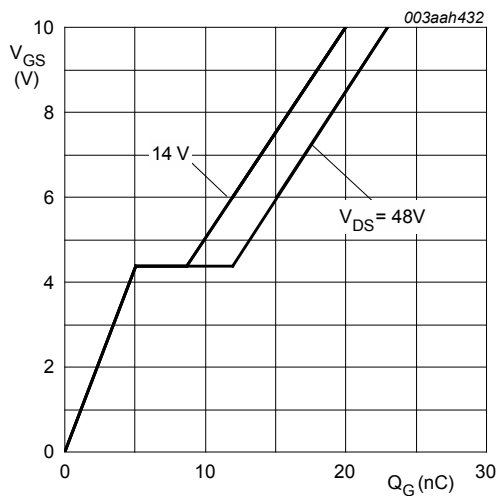


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^{\circ}C; I_D = 15A$

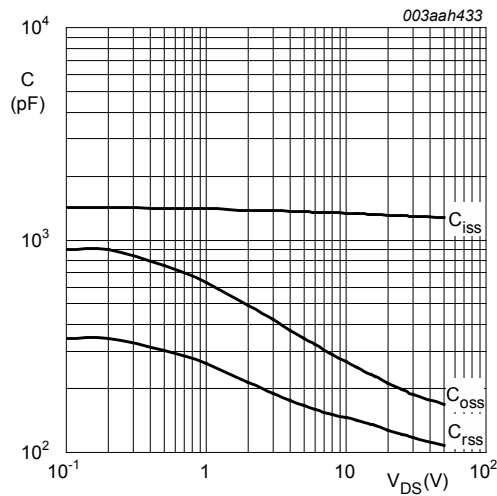


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

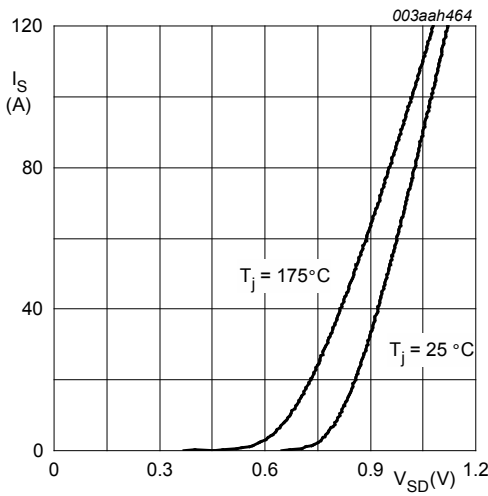


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

7. Package outline

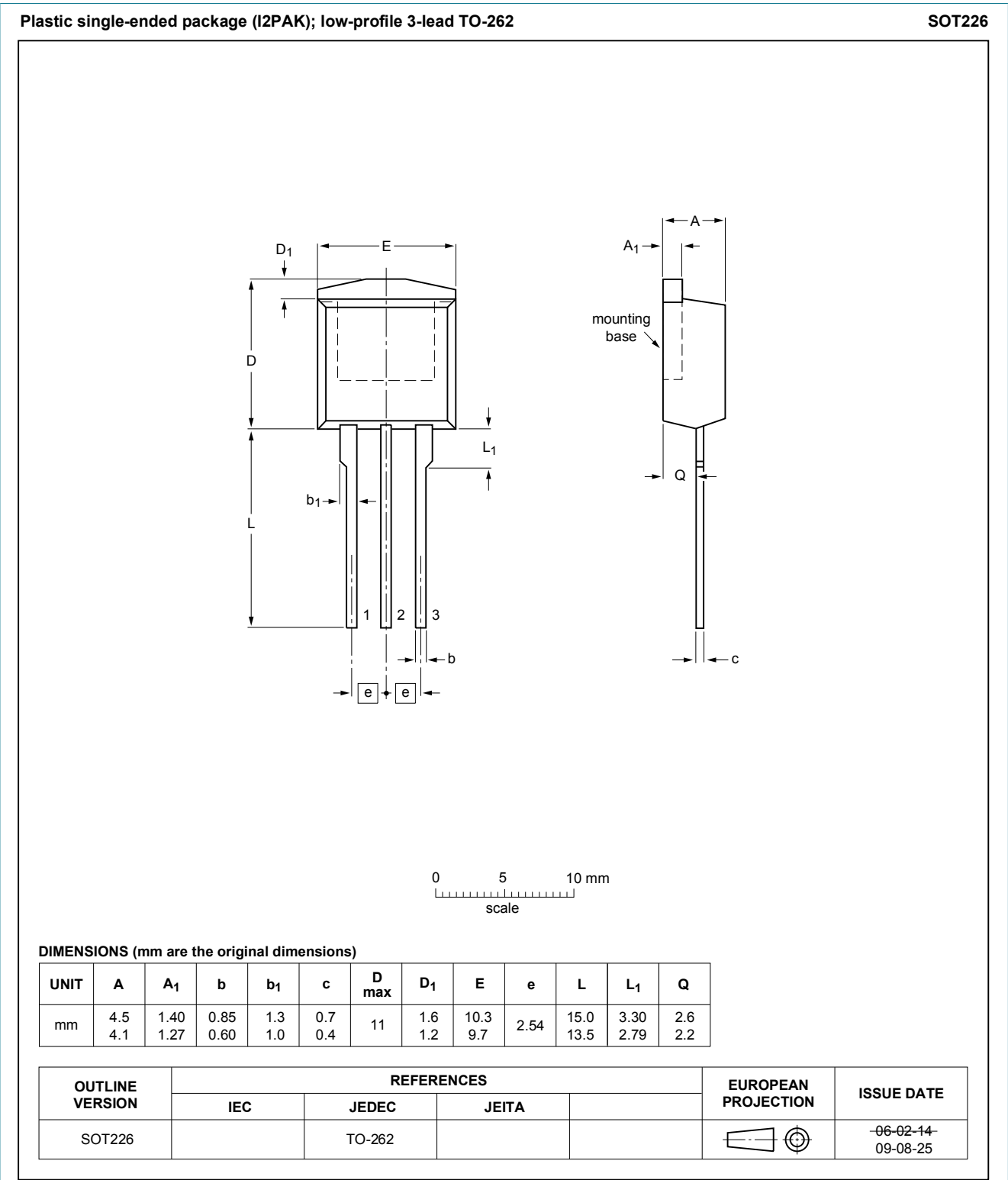


Fig. 17. Package outline I2PAK (SOT226)

## 8. Legal information

### 8.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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